## BAS316WS

## Silicon Epitaxial Planar Switching Diode

## Applications

- High-speed switching

PINNING

| PIN | DESCRIPTION |
| :---: | :--- |
| 1 | Cathode |
| 2 | Anode |



Absolute Maximum Ratings ( $\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C}$ )

| Parameter |  | Symbol | Value | Unit |
| :---: | :---: | :---: | :---: | :---: |
| Repetitive Peak Reverse Voltage |  | $V_{\text {RRM }}$ | 100 | V |
| Reverse Voltage |  | $\mathrm{V}_{\mathrm{R}}$ | 100 | V |
| Continuous Forward Current |  | $\mathrm{I}_{\mathrm{F}}$ | 250 | mA |
| Repetitive Peak Forward Current |  | $\mathrm{I}_{\text {FRM }}$ | 500 | mA |
| Non-Repetitive Peak Forward Current | $\begin{aligned} & \mathrm{t}=1 \mu \mathrm{~s} \\ & \mathrm{t}=1 \mathrm{~ms} \\ & \mathrm{t}=1 \mathrm{~s} \end{aligned}$ | $\mathrm{I}_{\text {FSM }}$ | $\begin{gathered} \hline 4 \\ 1 \\ 0.5 \end{gathered}$ | A |
| Total Power Dissipation |  | $\mathrm{P}_{\text {tot }}$ | 200 | mW |
| Junction Temperature |  | $\mathrm{T}_{\mathrm{j}}$ | 150 | ${ }^{\circ} \mathrm{C}$ |
| Storage Temperature Range |  | $\mathrm{T}_{\text {stg }}$ | -65 to +150 | ${ }^{\circ} \mathrm{C}$ |

Characteristics at $\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C}$

| Parameter | Symbol | Max. | Unit |
| :---: | :---: | :---: | :---: |
| $\begin{aligned} & \text { Forward Voltage } \\ & \text { at } I_{F}=1 \mathrm{~mA} \\ & \text { at } I_{F}=10 \mathrm{~mA} \\ & \text { at } I_{F}=50 \mathrm{~mA} \\ & \text { at } I_{F}=150 \mathrm{~mA} \end{aligned}$ | $V_{F}$ | $\begin{gathered} 0.715 \\ 0.855 \\ 1 \\ 1.25 \end{gathered}$ | V |
| $\begin{aligned} & \text { Reverse Current } \\ & \text { at } \mathrm{V}_{R}=25 \mathrm{~V} \\ & \text { at } \mathrm{V}_{R}=75 \mathrm{~V} \\ & \text { at } \mathrm{V}_{R}=25 \mathrm{~V}, \mathrm{~T}_{J}=150^{\circ} \mathrm{C} \\ & \text { at } \mathrm{V}_{R}=75 \mathrm{~V}, \mathrm{~T}_{J}=150^{\circ} \mathrm{C} \end{aligned}$ | $I_{R}$ | $\begin{gathered} 30 \\ 1 \\ 30 \\ 50 \end{gathered}$ | nA <br> $\mu \mathrm{A}$ <br> $\mu \mathrm{A}$ <br> $\mu \mathrm{A}$ |
| Diode Capacitance at $\mathrm{V}_{\mathrm{R}}=0 \mathrm{~V}, \mathrm{f}=1 \mathrm{MHz}$ | $\mathrm{C}_{\text {tot }}$ | 1.5 | pF |
| Reverse Recovery Time at $I_{F}=I_{R}=10 \mathrm{~mA}, I_{r r}=0.1 \mathrm{XI}, \mathrm{I}_{\mathrm{L}}=100 \Omega$ | $\mathrm{t}_{\mathrm{rr}}$ | 4 | ns |



Fig. 1 Maximum permissible continuous forward current as a function of soldering point temperature.

(1) $\mathrm{T}_{\mathrm{J}}=150^{\circ} \mathrm{C}$; typical values.
(2) $\mathrm{T}_{1}=25^{\circ} \mathrm{C}$; typical values.
(3) $\mathrm{T}_{\mathrm{l}}=25^{\circ} \mathrm{C}$; maximum values.

Fig. 2 Forward current as a function of forward voltage.


Based on square wave currents.
$\mathrm{T}_{1}=25^{\circ} \mathrm{C}$ prior to surge.
Fig. 3 Maximum permissible non-repetitive peak forward current as a function of pulse duration.


Fig. 4 Reverse current as a function of junction temperature.

$\mathrm{f}=1 \mathrm{MHz} ; \mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$
Fig. 5 Diode capacitance as a function of reverse voltage; typical values.

## PACKAGE OUTLINE



| Symbol | Dimension in Millimeters |  |
| :---: | :---: | :---: |
|  | Min | Max |
| A | 0.90 | 1.20 |
| bp | 0.25 | 0.40 |
| C | 0.10 | 0.15 |
| D | 1.60 | 1.80 |
| E | 1.15 | 1.35 |
| HE | 2.30 | 2.80 |
| A1 | 0.01 | 0.10 |
| Lp | 0.20 | 0.50 |

